



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

35 A

Features

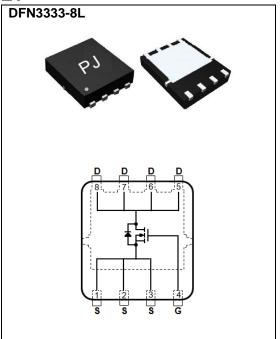
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@15A<25m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<28.5mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard



• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	.,,	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	I _D	35	А	
	T _C =100°C		22		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	140		
Power Dissipation	T _C =25°C	PD	62	10/	
	T _C =100°C		25	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	6.3		
	T _A =70°C		5	Α	
Power Dissipation	T _A =25°C	Po	2.0	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	54	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.73	2.5			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A	-	20	25	mΩ		
		V _{GS} =4.5V, I _D =10A	-	22	28.5			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V	-	-	1	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 5)								
Total Gate Charge	Q_g	V 50V I 40A	-	31	-	nC		
Gate-Source Charge	Q_gs	V_{DS} =50V, I_{D} =10A, V_{GS} =10V (Note 2,3)	-	5.1	-			
Gate-Drain Charge	Q_gd	V _{GS} =10V	-	7.3	-			
Input Capacitance	Ciss		-	1519	-	pF		
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, f=1MHZ	-	132	-			
Reverse Transfer Capacitance	Crss	I=IIVIIIZ	-	66	-			
Turn-On Delay Time	td _(on)	V 50V I 40A	-	11	-			
Turn-On Rise Time	t _r	V_{DD} =50V, I_{D} =10A,	-	42	-	ns		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V$, $R_{G}=3\Omega$ (Note 2,3)	-	40	-			
Turn-Off Fall Time	t _f	K _G =312	-	19	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,				35	А		
Diode Forward Current	I _S		-	_	30	^		
Reverse Recovery Time	V _{SD}	I _S =1A, V _{GS} =0V	-	0.68	1.2	V		

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=3mH, I_{AS} =6A, V_{DD} =50V, V_{GS} =10V, Starting T_{J} =25 $^{\circ}$ C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

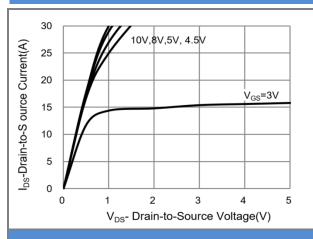


Fig.1 On-Region Characteristics

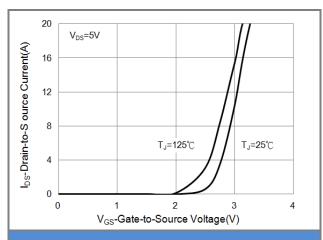


Fig.2 Transfer Characteristics

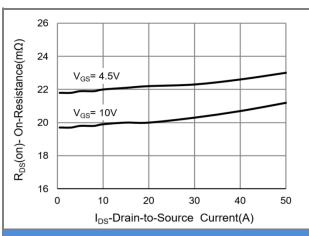


Fig.3 On-Resistance vs. Drain Current

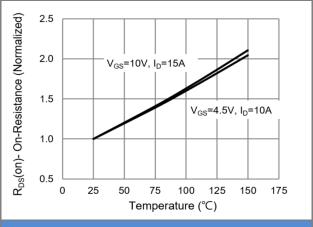


Fig.4 On-Resistance vs. Junction temperature

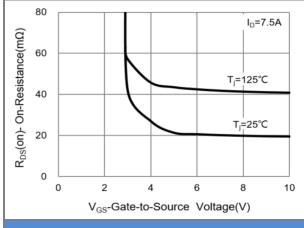


Fig.5 On-Resistance Variation with V_{GS}

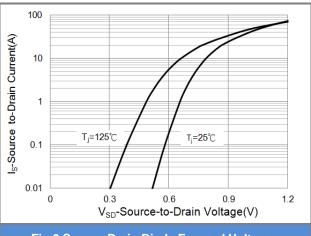


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

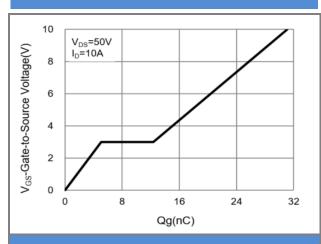


Fig.7 Gate-Charge Characteristics

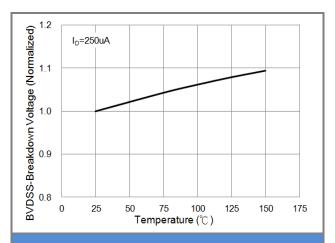


Fig.8 Breakdown Voltage Variation vs. Temperature

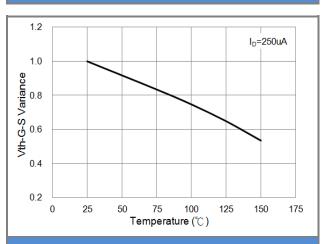


Fig.9 Threshold Voltage Variation with Temperature

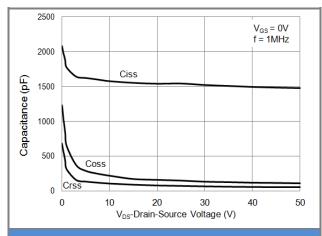
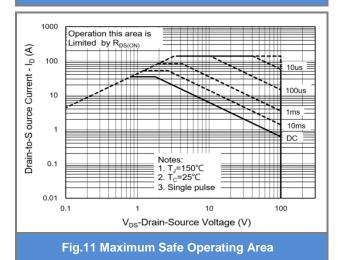


Fig.10 Capacitance vs. Drain-Source Voltage



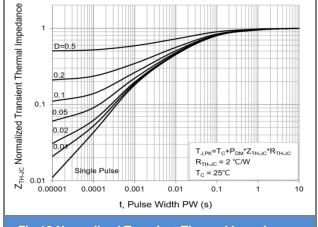


Fig.12 Normalized Transient Thermal Impedance

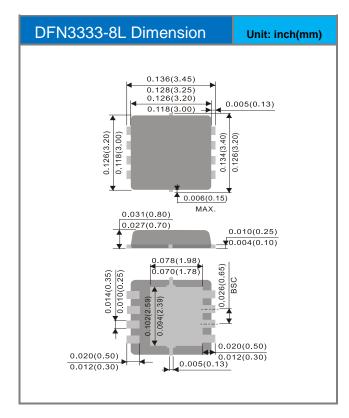


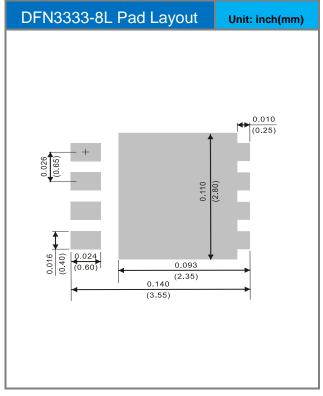


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ4476AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4476	Halogen free	

Packaging Information & Mounting Pad Layout









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